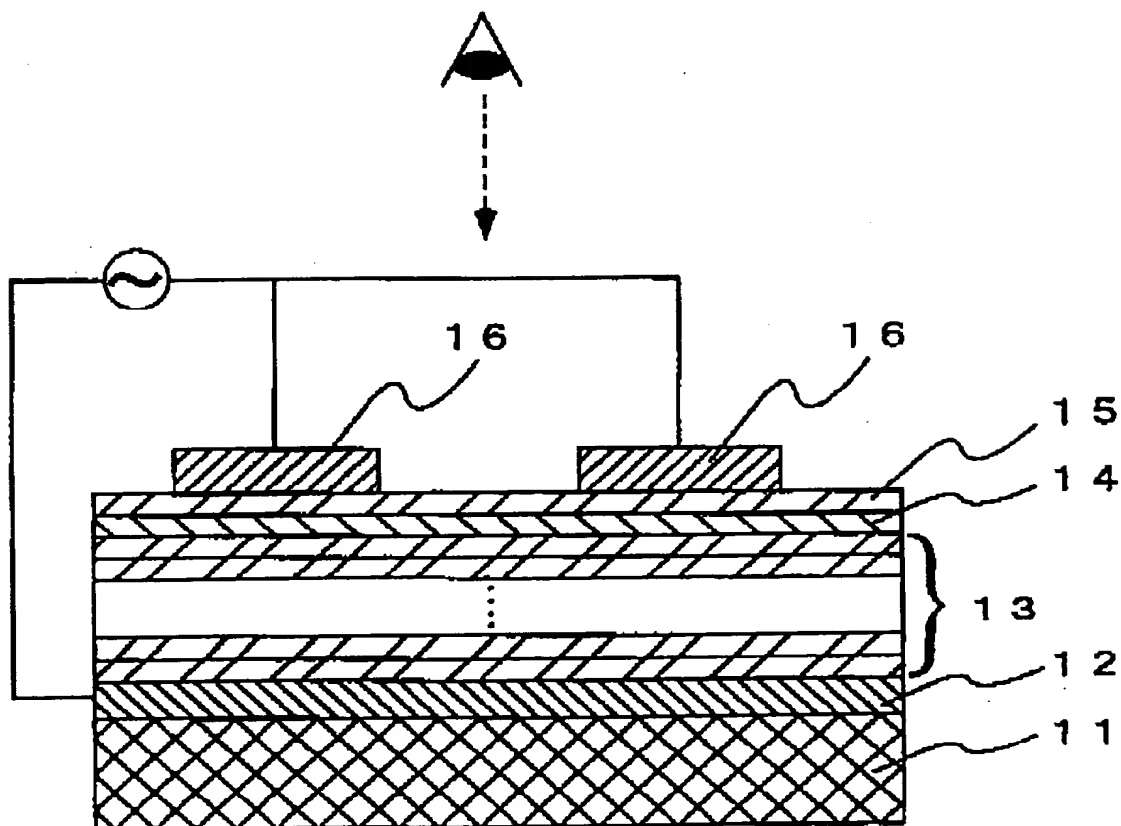
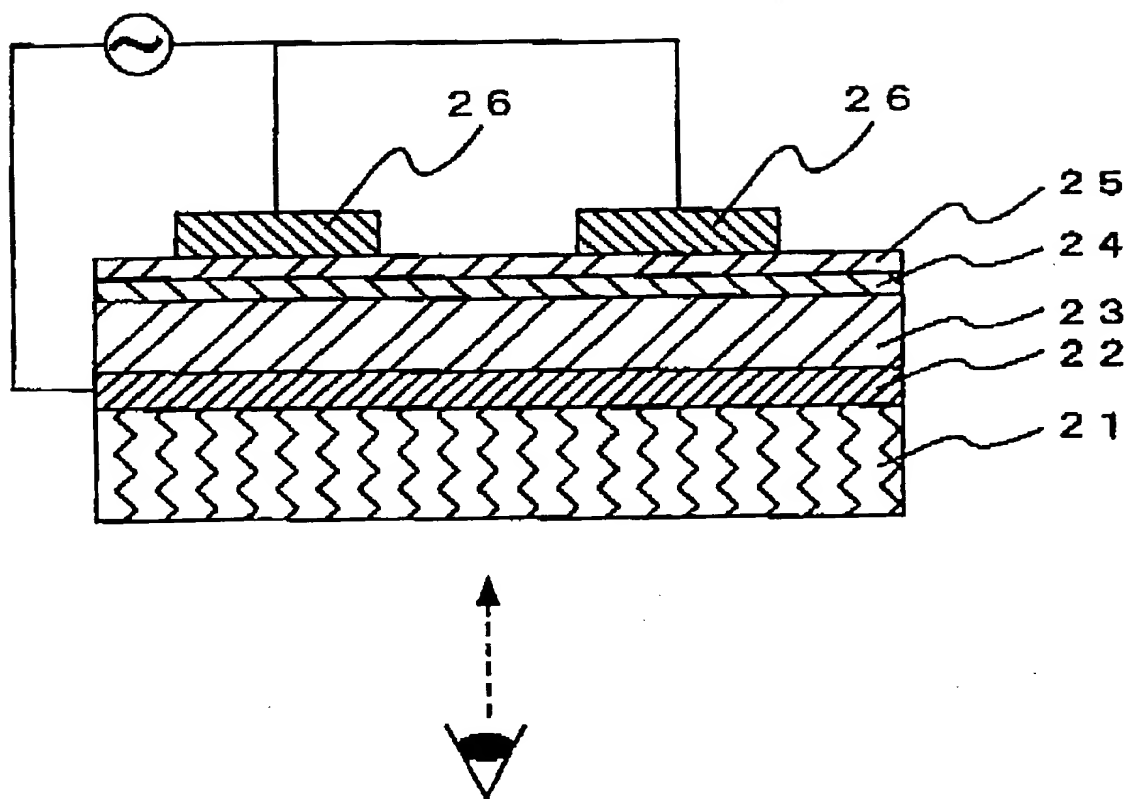


FIG. 1



00966733 063004

FIG. 2



A cross-sectional view of a semiconductor device. The device consists of a substrate (31) with a cross-hatched pattern, a thin layer (32) on top of it, a layer (33) with diagonal hatching, a thick layer (34) with diagonal hatching, and a top layer (35). Two rectangular regions (36) are located on the top layer (35). These regions are connected to a circuit that includes an AC power source (represented by a circle with a tilde symbol) and a dashed arrow pointing upwards towards a lens-like structure above the device.

FIG. 4A

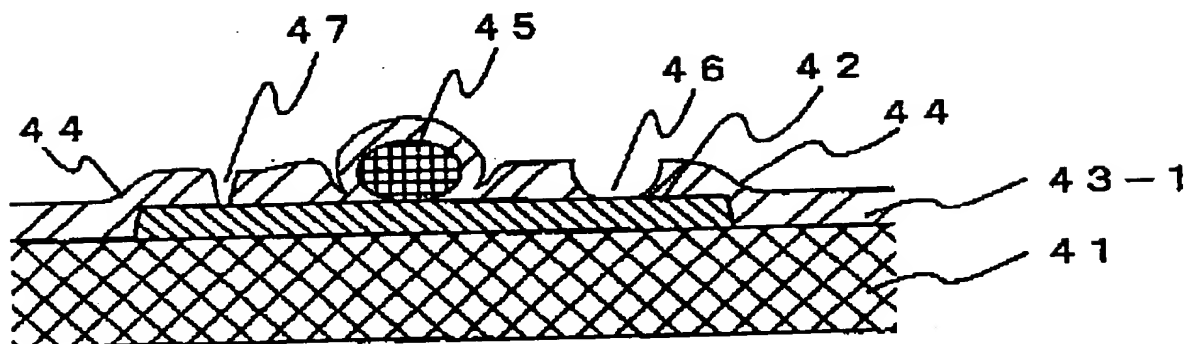


FIG. 4B

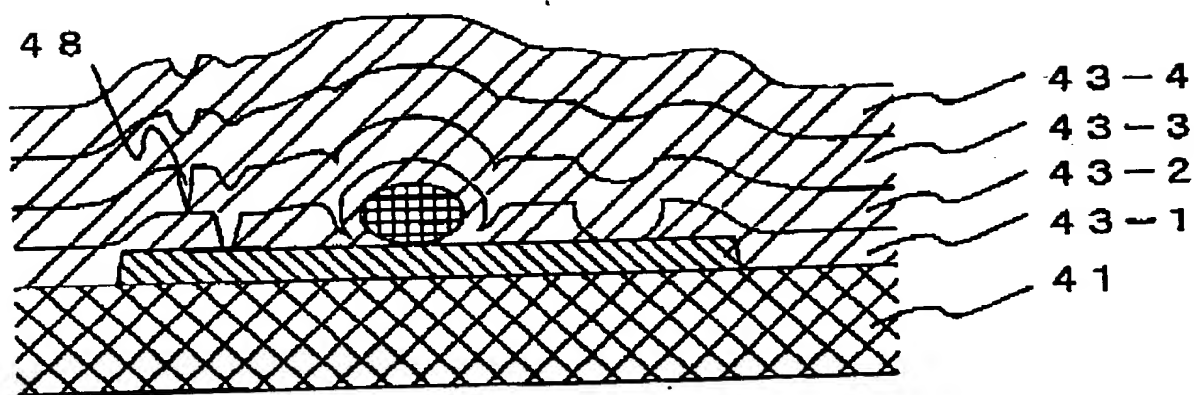
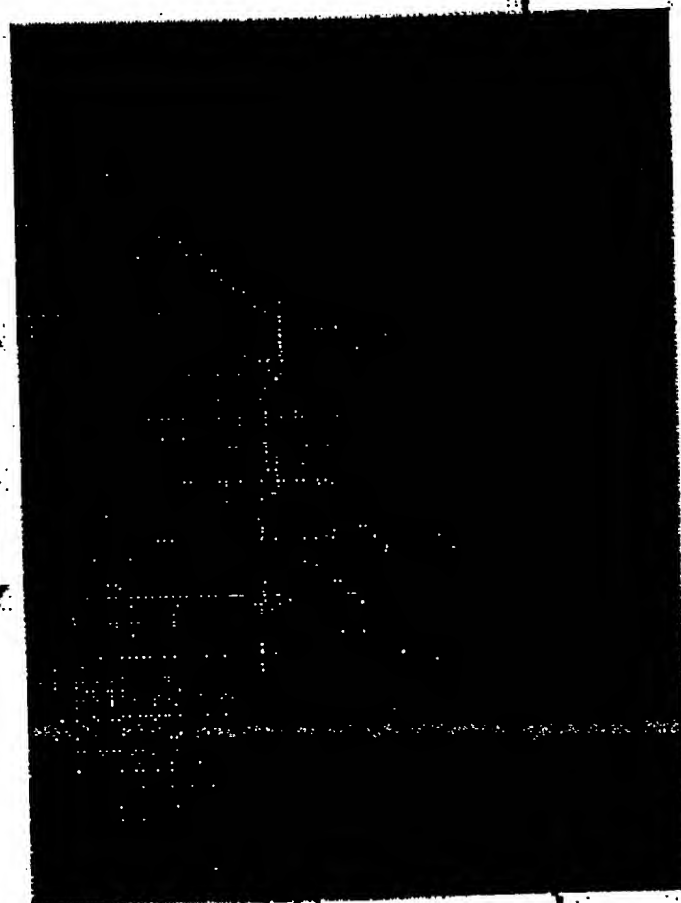


FIG. 5

10 μ m



BaTiO₃膜

電極

基板

電極

FIG. 6

100 μ m

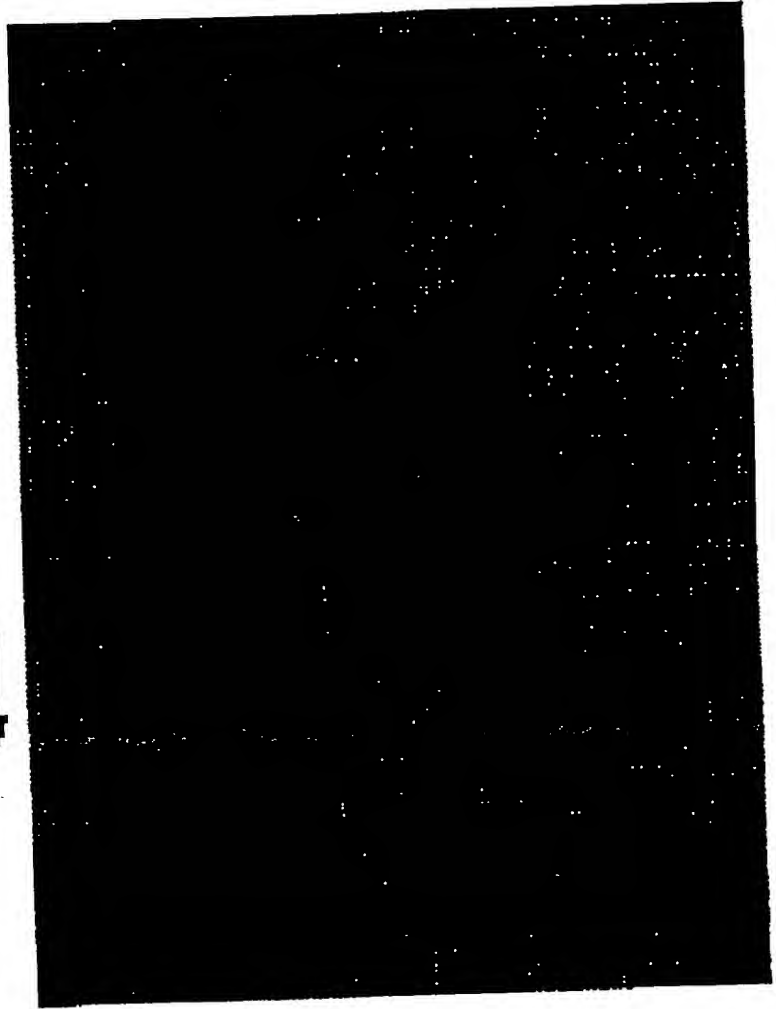


FIG. 7

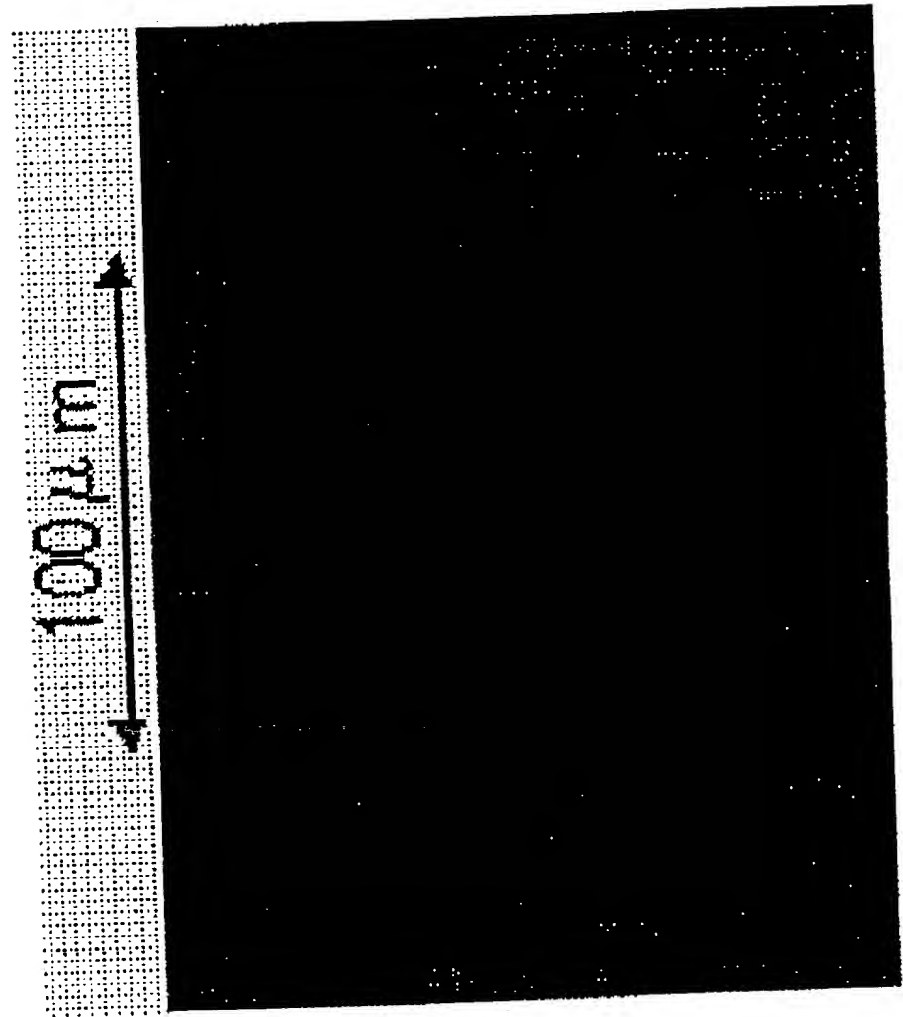


FIG. 8

100 μ m

